

MSB190N10

N-Channel 100-V (D-S) MOSFET

Description

The MSB190N10 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-263 package is universally preferred for all commercial-industrial applications

Features

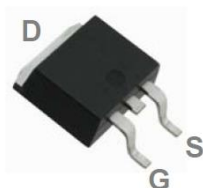
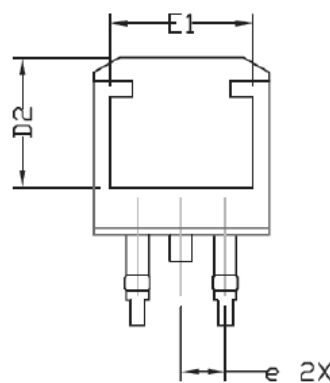
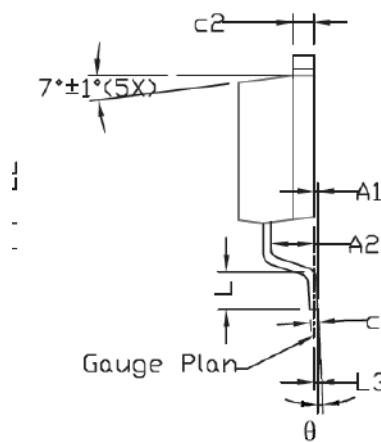
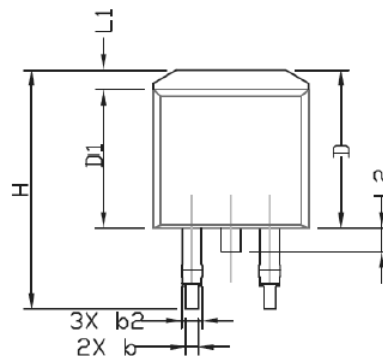
- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed
- RoHS compliant package

Application

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

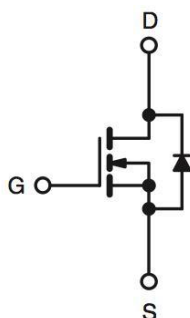
Packing & Order Information

50/Tube ; 1,000/Box



**RoHS
COMPLIANT**

Graphic symbol



TO-263						
Symbol	Dimensional Reqmts			Inches Reqmts		
	Min	Nom	Max	Min	Nom	Max
A	4.3	4.57	4.72	0.169	0.180	0.186
A1	0	-	0.25	0.000	-	0.010
A2	2.47	2.57	2.67	0.097	0.101	0.105
b	0.69	0.813	0.94	0.027	0.032	0.037
b2	1.17	1.27	1.45	0.046	0.050	0.057
c	0.48	0.5	0.6	0.019	0.020	0.024
c2	1.17	1.27	1.37	0.046	0.050	0.054
D	9.8	10.05	10.3	0.386	0.396	0.406
D1	8.64	8.78	9.65	0.340	0.346	0.380
D2	7.12	7.37	7.62	0.280	0.290	0.300
e	9.7	10.15	10.54	0.382	0.400	0.415
e1	8	8.2	8.4	0.315	0.323	0.331
E	2.54 BSC			0.100 BSC		
H	14.99	15.24	15.49	0.590	0.600	0.610
L	1.78	2.29	2.79	0.070	0.090	0.110
L1	1.02	1.27	1.52	0.040	0.050	0.060
L2	-	-	1.75	-	-	0.069
L3	-	0.254	-	-	0.010	-
θ	0°C	-	8°C	0°C	-	8°C

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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current ^a ($T_C=25^{\circ}\text{C}$)	190	A
	Continuous Drain Current ^a ($T_C=70^{\circ}\text{C}$)	158	A
I_{DM}	Pulsed Drain Current ^b	750	A
I_S	Continuous Source Current (Diode Conduction) ^a	190	A
P_D	Power Dissipation ^a ($T_C=25^{\circ}\text{C}$)	300	W
	Power Dissipation ^a ($T_C=70^{\circ}\text{C}$)	150	W
T_J/T_{STG}	Operating Junction and Storage Temperature	-55 to +175	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

Symbol	Parameter	Maximum	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ^a	62.5	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Maximum Junction-to-Case	0.5	

Notes

- Package Limited
- Pulse width limited by maximum junction temperature
- Surface Mounted on 1" x 1" FR4 Board.

Static

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
V_{GS}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	1			V
I_{GSS}	Gate-Body Leakage	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^{\circ}\text{C}$			1 10	μA
$I_{D(on)}$	On-State Drain Current ^A	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	240			A
$R_{DS(on)}$	Drain-Source On-Resistance ^A	$V_{GS} = 10\text{ V}, I_D = 45\text{ A}$ $V_{GS} = 5.5\text{ V}, I_D = 44\text{ A}$			4 5.5	m Ω
g_{fs}	Forward Transconductance ^A	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		19		S
V_{SD}	Diode Forward Voltage	$I_S = 95\text{ V}, V_{GS} = 0\text{ V}$		1		V

Dynamic^b

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 50\text{ V}, R_L = 2.5\ \Omega,$ $V_{GEN} = 10\text{ V}, R_{GEN} = 6\ \Omega,$ $I_D = 20\text{ A}$	--	38	--	ns
t_r	Rise Time		--	25	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	283	--	ns
t_f	Fall Time		--	60	--	ns

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Dynamic ^b						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
Q_g	Total Gate Charge	$V_{DS} = 50\text{ V}$, $I_D = 20\text{ A}$ $V_{GS} = 5.5\text{ V}$	--	140	--	nC
Q_{gs}	Gate-Source Charge		--	50	--	nC
Q_{gd}	Gate-Drain Charge		--	33	--	nC
C_{iss}	Input Capacitance	$V_{GS} = 0\text{ V}$, $V_{DS} = 15\text{ V}$, $f = 1\text{ MHz}$	--	12354	--	pF
C_{oss}	Output Capacitance		--	516	--	pF
C_{rss}	Reverse Transfer Capacitance		--	422	--	pF

Notes

- Pulse test: $PW \leq 300\mu s$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics

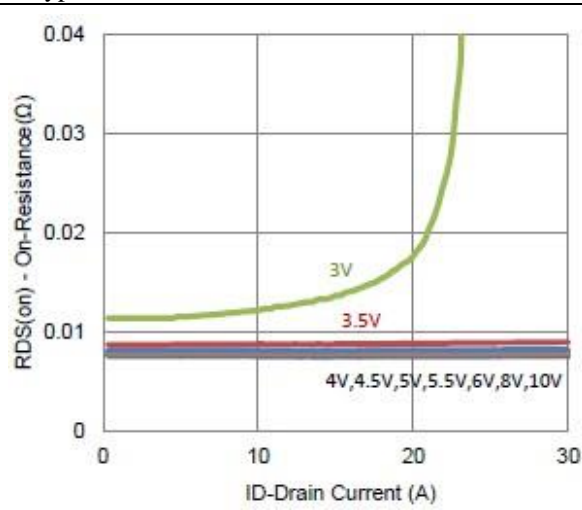


FIG.1-ON-RESISTANCE VS. DRAIN CURRENT

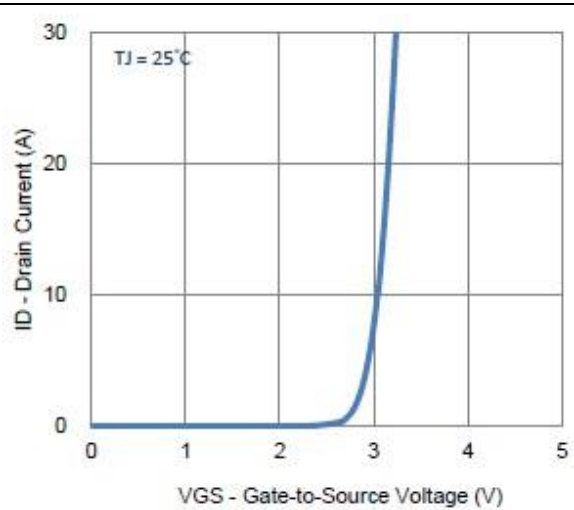


FIG.2-TRANSFER CHARACTERISTICS

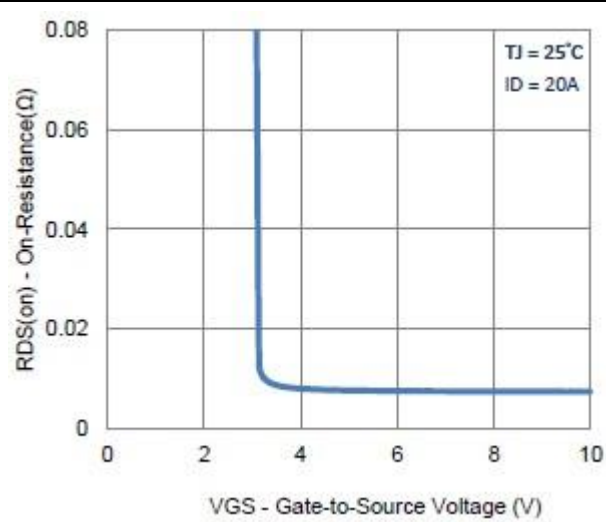


FIG.3- ON-RESISTANCE VS. GATE-TO-SOURCE VOLTAGE

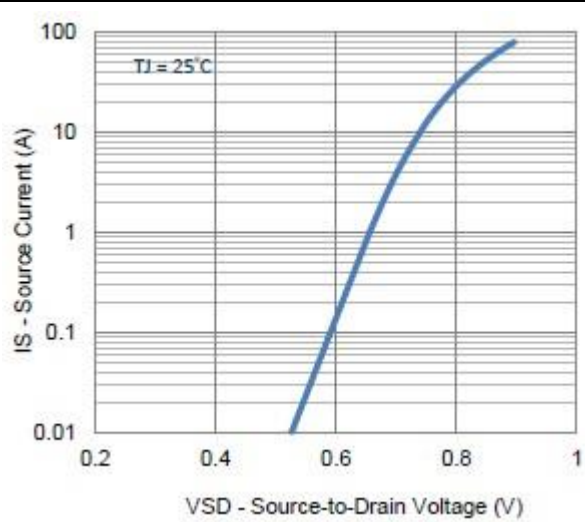


FIG.4-DRAIN TO SOURCE FORWARD VOLTAGE

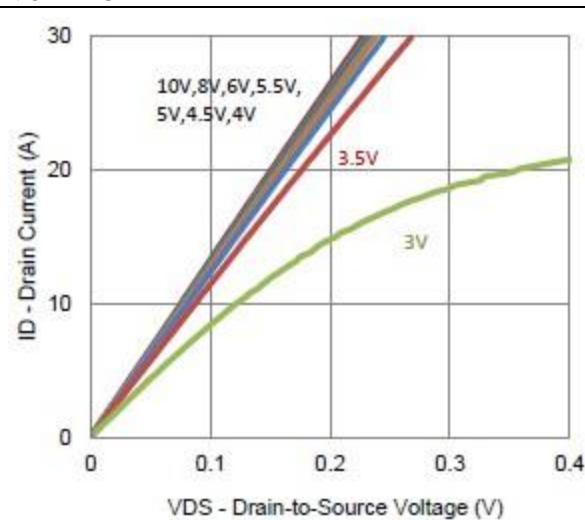


FIG.5-OUTPUT CHARACTERISTICS

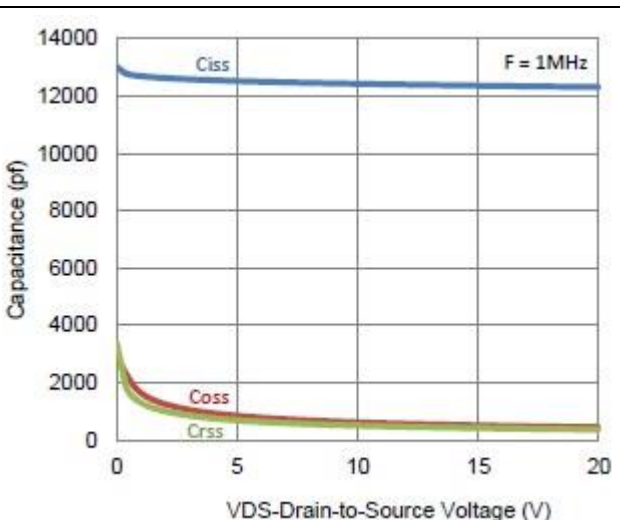


FIG.6-CAPACITANCE

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Typical Electrical Characteristics

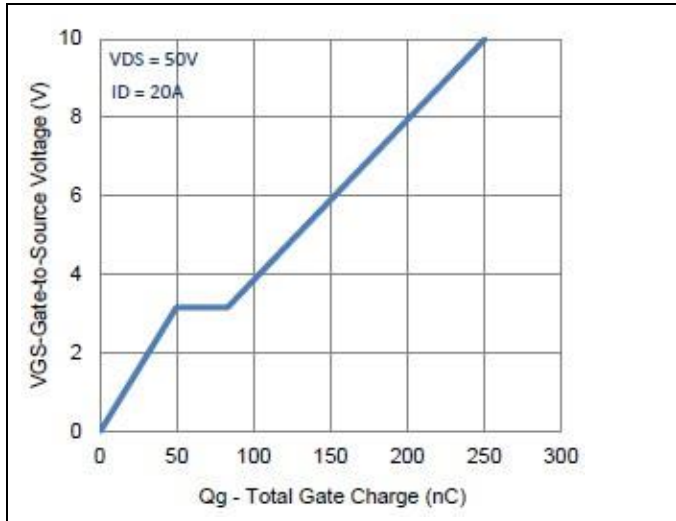


FIG.7-GATE CHARGE

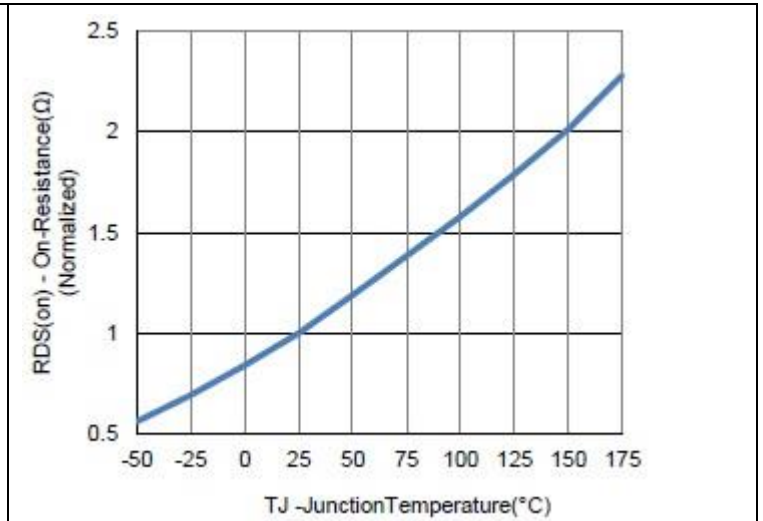


FIG.8-NORMALIZED ON-RESISTANCE VS JUNCTION TEMPERATURE

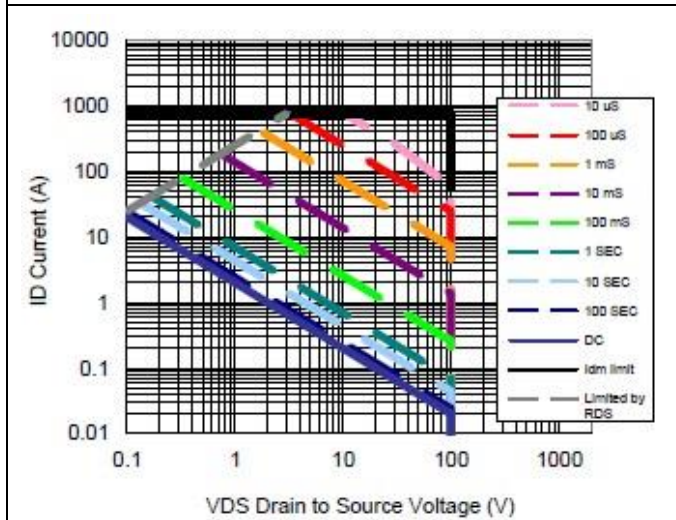


FIG.9-SAFE OPERATING AREA

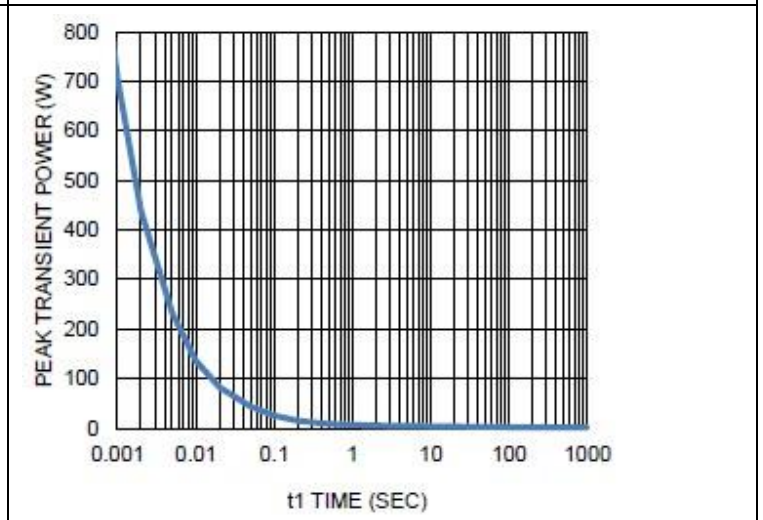


FIG.10-SINGLE PULSE MAXIMUM POWER DISSIPATION

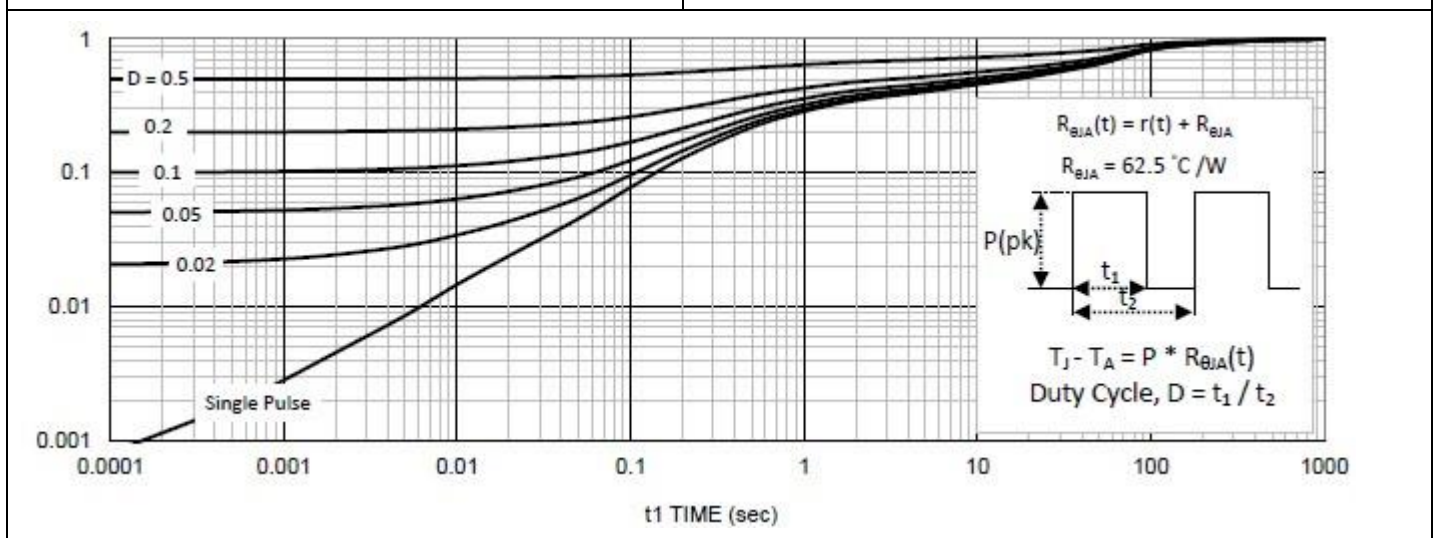


FIG.11-NORMALIZED THERMAL TRANSIENT JUNCTION TO AMBIENT

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